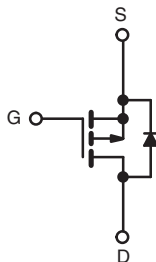
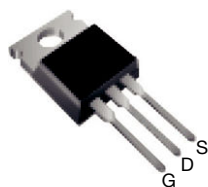


Power MOSFET

PRODUCT SUMMARY

V_{DS} (V)	- 50	
$R_{DS(on)}$ (Ω)	$V_{GS} = - 10$ V	0.14
Q_g (Max.) (nC)	39	
Q_{gs} (nC)	10	
Q_{gd} (nC)	15	
Configuration	Single	

TO-220AB


P-Channel MOSFET

FEATURES

- P-Channel Versatility
- Compact Plastic Package
- Fast Switching
- Low Drive Current
- Ease of Paralleling
- Excellent Temperature Stability
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

Note

* Lead (Pb)-containing terminations are not RoHS-compliant. Exemptions may apply.


RoHS*
COMPLIANT

DESCRIPTION

The power MOSFET technology is the key to Vishay's advanced line of power MOSFET transistors. The efficient geometry and unique processing of the power MOSFET design achieve very low on-state resistance combined with high transconductance and extreme device ruggedness.

The p-channel power MOSFET's are designed for application which require the convenience of reverse polarity operation. They retain all of the features of the more common n-channel Power MOSFET's such as voltage control, very fast switching, ease of paralleling, and excellent temperature stability.

P-channel power MOSFETs are intended for use in power stages where complementary symmetry with n-channel devices offers circuit simplification. They are also very useful in drive stages because of the circuit versatility offered by the reverse polarity connection. Applications include motor control, audio amplifiers, switched mode converters, control circuits and pulse amplifiers.

ORDERING INFORMATION

Package	TO-220AB
Lead (Pb)-free	IRF9Z30PbF
	SiHF9Z30-E3
SnPb	IRF9Z30
	SiHF9Z30

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	- 50	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	$T_C = 25^\circ\text{C}$	A
		$T_C = 100^\circ\text{C}$	
Pulsed Drain Current ^a	I_{DM}	- 60	
Linear Derating Factor		0.59	W/ $^\circ\text{C}$
Inductive Current, Clamped	I_{LM}	- 60	A
Unclamped Inductive Current (Avalanche Current)	I_L	- 3.1	A
Maximum Power Dissipation	P_D	74	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	$^\circ\text{C}$
Soldering Recommendations (Peak Temperature)	for 10 s	300 ^c	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 14).
- $V_{DS} = - 25$ V, starting $T_J = 25^\circ\text{C}$, $L = 100\ \mu\text{H}$, $R_g = 25\ \Omega$
- 0.063" (1.6 mm) from case.

**THERMAL RESISTANCE RATINGS**

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	80	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	1.7	

SPECIFICATIONS ($T_J = 25\text{ °C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = -250\text{ }\mu\text{A}$		- 50	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\text{ }\mu\text{A}$		- 2.0	-	- 4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$		-	-	± 500	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = \text{max. rating}$, $V_{GS} = 0\text{ V}$		-	-	- 250	μA
		$V_{DS} = \text{max. rating} \times 0.8$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$		-	-	- 1000	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = -10\text{ V}$	$I_D = -9.3\text{ A}^b$	-	0.093	0.14	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 2 \times V_{GS}$, $I_{DS} = -9\text{ A}^b$		3.1	4.7	-	S
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = -25\text{ V}$, $f = 1.0\text{ MHz}$, see fig. 9		-	900	-	pF
Output Capacitance	C_{oss}			-	570	-	
Reverse Transfer Capacitance	C_{rss}			-	140	-	
Total Gate Charge	Q_g	$V_{GS} = -10\text{ V}$	$I_D = -18\text{ A}$, $V_{DS} = -0.8$ max. rating, see fig. 17	-	26	39	nC
Gate-Source Charge	Q_{gs}			-	6.9	10	
Gate-Drain Charge	Q_{gd}			-	9.7	15	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -25\text{ V}$, $I_D = -18\text{ A}$, $R_g = 13\text{ }\Omega$, $R_D = 1.3\text{ }\Omega$, see fig. 16 (MOSFET switching times are essentially independent of operating temperature)		-	12	18	ns
Rise Time	t_r			-	110	170	
Turn-Off Delay Time	$t_{d(off)}$			-	21	32	
Fall Time	t_f			-	64	96	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	- 18	A
Pulsed Diode Forward Current ^a	I_{SM}			-	-	- 60	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}$, $I_S = -18\text{ A}$, $V_{GS} = 0\text{ V}^b$		-	-	- 6.3	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}$, $I_F = -18\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}^b$		54	120	250	ns
Body Diode Reverse Recovery Charge	Q_{rr}			0.20	0.47	1.1	μC

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 14).
b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

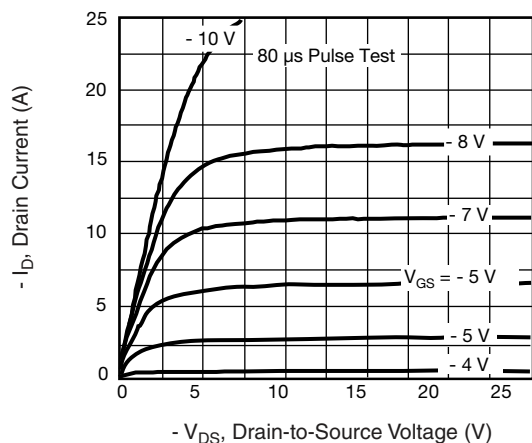


Fig. 1 - Typical Output Characteristics

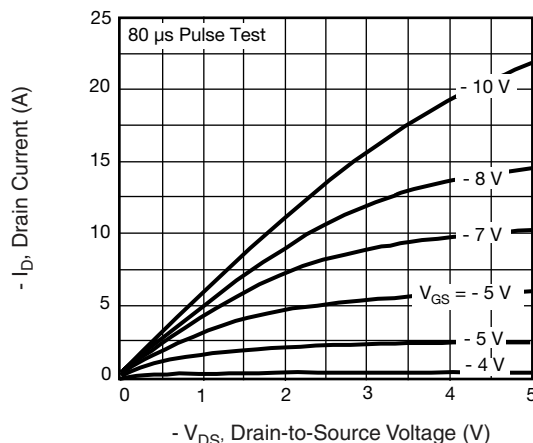


Fig. 3 - Typical Saturation Characteristics

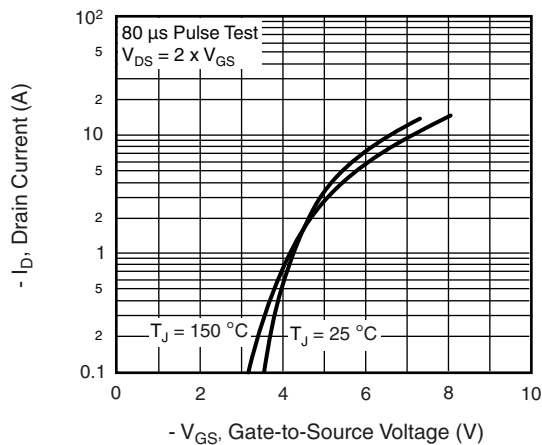


Fig. 2 - Typical Transfer Characteristics

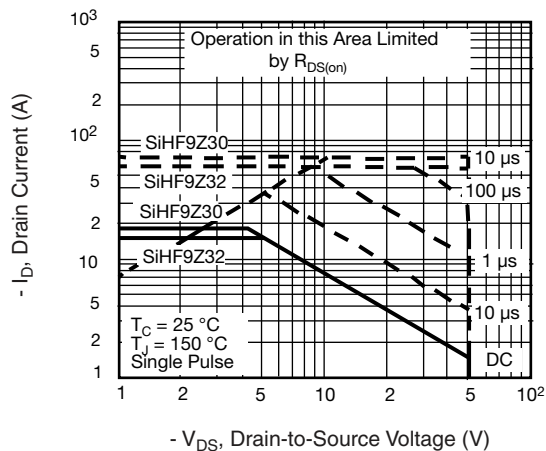
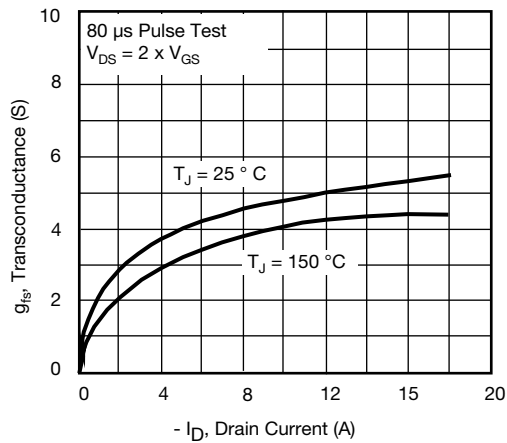
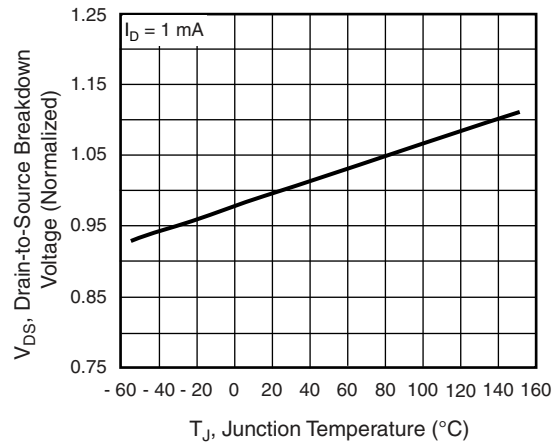
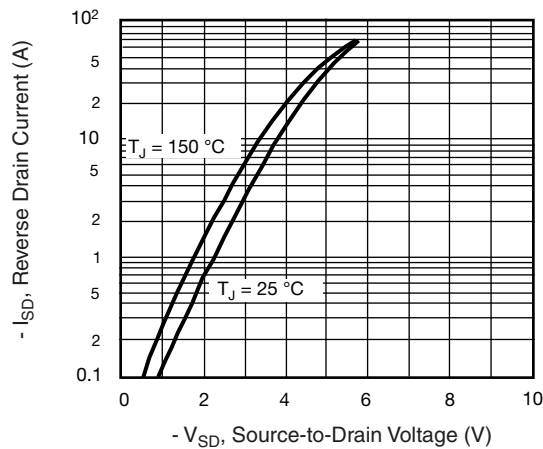
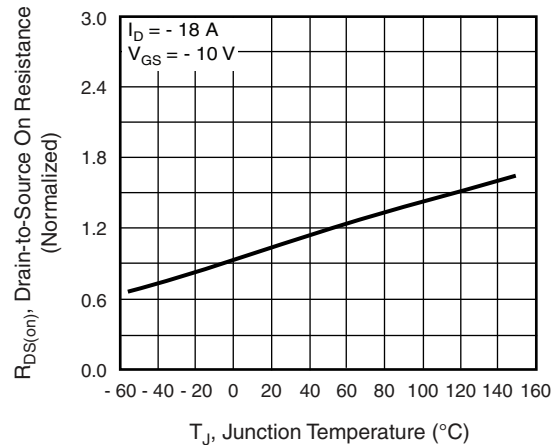
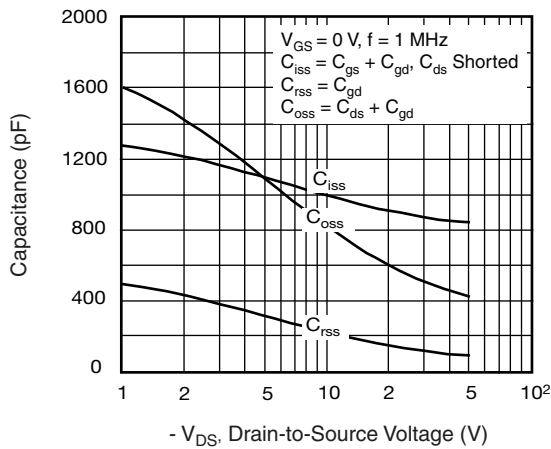
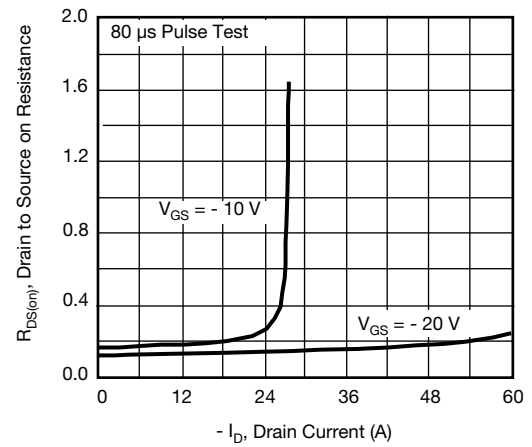
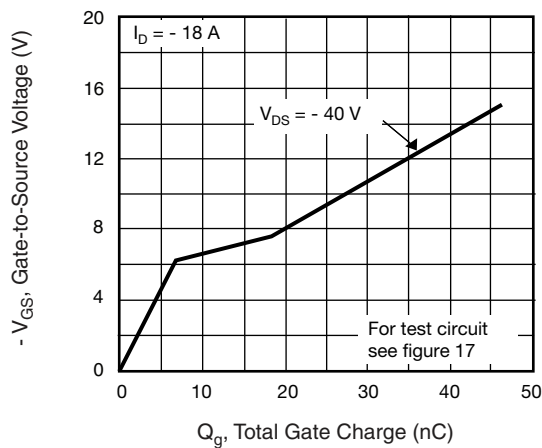
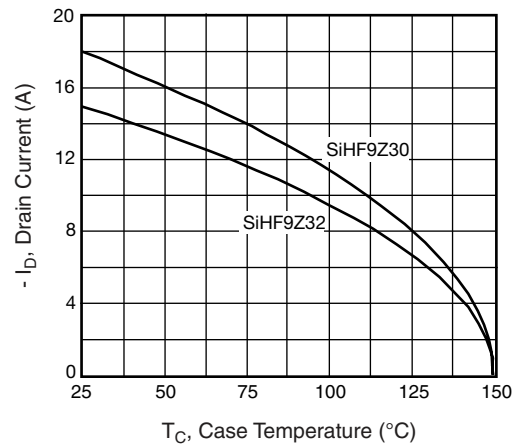
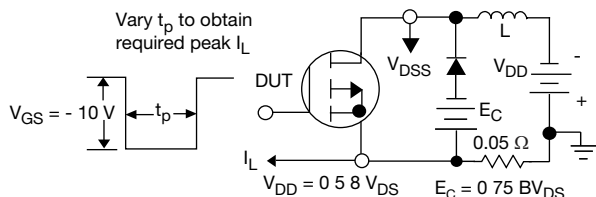
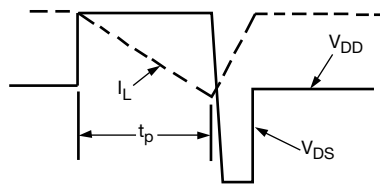
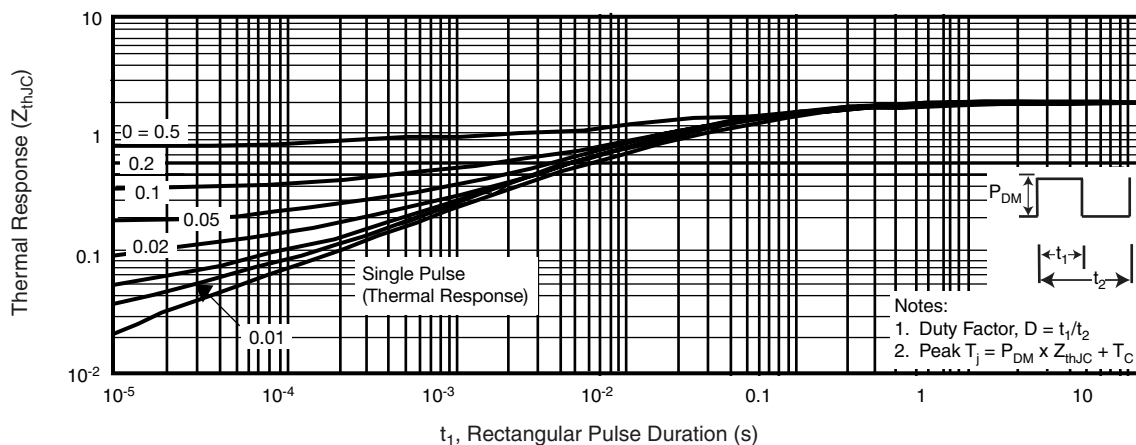
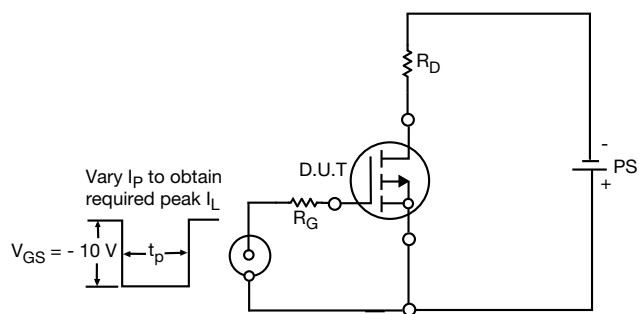
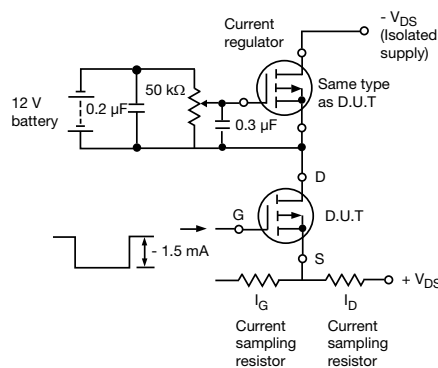


Fig. 4 - Maximum Safe Operating Area


Fig. 5 - Typical Transconductance vs. Drain Current

Fig. 7 - Breakdown Voltage vs. Temperature

Fig. 6 - Typical Source-Drain Diode Forward Voltage

Fig. 8 - Normalized On-Resistance vs. Temperature


Fig. 9 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 11 - Typical On-Resistance vs. Drain Current

Fig. 10 - Typical Gate Charge vs. Gate-to-Source Voltage

Fig. 12 - Maximum Drain Current vs. Case Temperature


Fig. 13a - Unclamped Inductive Test Circuit

Fig. 13b - Unclamped Inductive Load Test Waveforms

Fig. 14 - Maximum Effective Transient Thermal Impedance, Junction-to-Case vs. Pulse Duration

Fig. 15 - Switching Time Test Circuit

Fig. 16 - Gate Charge Test Circuit

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TO-220-1



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.24	4.65	0.167	0.183
b	0.69	1.02	0.027	0.040
b(1)	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.33	15.85	0.564	0.624
E	9.96	10.52	0.392	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.10	6.71	0.240	0.264
J(1)	2.41	2.92	0.095	0.115
L	13.36	14.40	0.526	0.567
L(1)	3.33	4.04	0.131	0.159
Ø P	3.53	3.94	0.139	0.155
Q	2.54	3.00	0.100	0.118

ECN: X15-0364-Rev. C, 14-Dec-15
DWG: 6031

Note

- M* = 0.052 inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM

Package Picture





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